

### GENERAL FEATURES

- $V_{DS} = -60V$   $I_D = -3.8A$
- $R_{DS(ON)} < -98m\Omega$  @  $V_{GS}=10V$
- $R_{DS(ON)} < -145m\Omega$  @  $V_{GS}=4.5V$

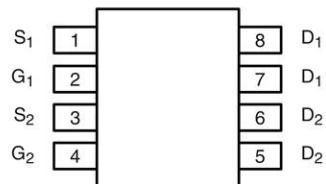
### Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

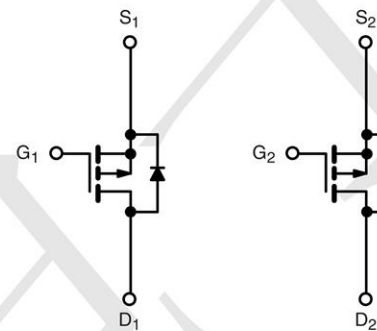
### Package and Pin Configuration



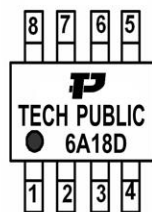
SOP-8 top view



### Circuit diagram



### Marking:



### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-60	V
Continuous Drain Current	$I_D$	-3.8	A
Pulsed Drain Current (note1)	$I_{DM}$	-16	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	36	mJ
Avalanche Current	$I_{AS}$	12	A
Power Dissipation ( $T_C = 25^\circ C$ ) (note3)	$P_D$	2.3	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 To 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient <sup>3</sup>	Max. 40	$^\circ C/W$

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Specifications T <sub>J</sub> = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-60	--	--	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 25°C	--	--	-1	μA
		V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C	--	--	-100	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1.0	-1.7	-3.0	V
Drain-Source On-Resistance (Note3)	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4A	--	90	98	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3A	--	100	145	mΩ
<b>Dynamic</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -30V, f = 1.0MHz	--	976	--	pF
Output Capacitance	C <sub>oss</sub>		--	70	--	
Reverse Transfer Capacitance	C <sub>rss</sub>		--	30	--	
Total Gate Charge	Q <sub>g</sub>	V <sub>DD</sub> = -30V, I <sub>D</sub> = -4A, V <sub>GS</sub> = -10V	--	24	--	nC
Gate-Source Charge	Q <sub>gs</sub>		--	2.2	--	
Gate-Drain Charge	Q <sub>gd</sub>		--	3.6	--	
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -30V, I <sub>D</sub> = -4A, R <sub>G</sub> = 2.5Ω	--	10	--	ns
Turn-on Rise Time	t <sub>r</sub>		--	5	--	
Turn-off Delay Time	t <sub>d(off)</sub>		--	35	--	
Turn-off Fall Time	t <sub>f</sub>		--	9	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25°C	--	--	-3.8	A
Pulsed Diode Forward Current	I <sub>SM</sub>		--	--	-16	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25°C, I <sub>SD</sub> = -4A, V <sub>GS</sub> = 0V	--	--	-1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -4A, di <sub>F</sub> /dt = 100A/μs	--	36	--	ns
Reverse Recovery Charge	Q <sub>rr</sub>		--	38	--	nC

Typical Electrical and Thermal Characteristics

Figure 1. Output Characteristics

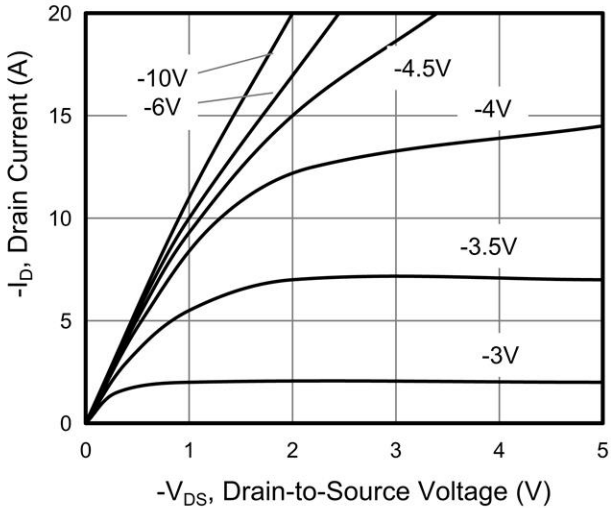


Figure 2. Transfer Characteristics

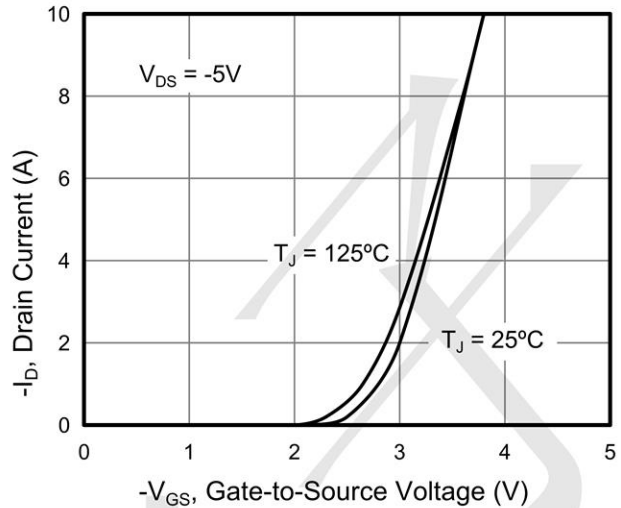


Figure 3. On-Resistance vs. Drain Current

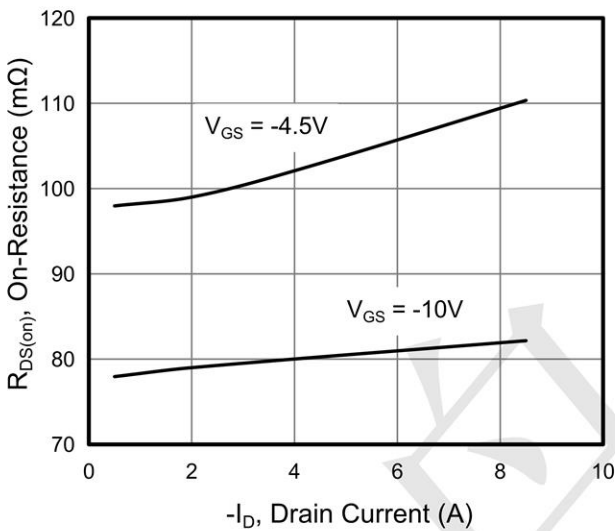


Figure 4. On-Resistance vs. Junction Temperature

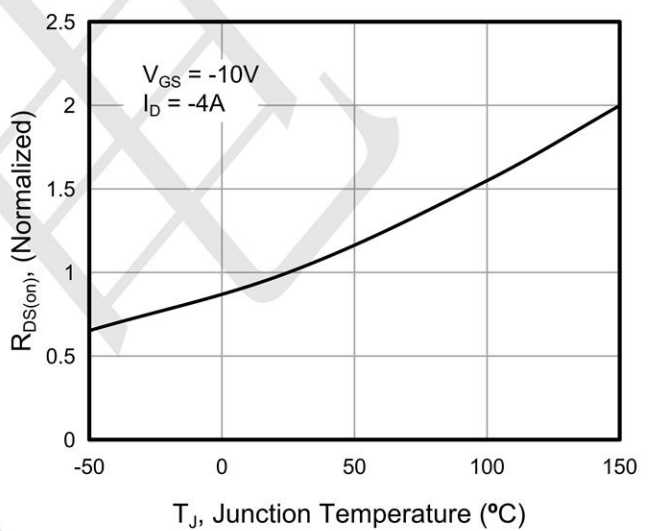


Figure 5. Threshold Voltage vs. Junction Temperature

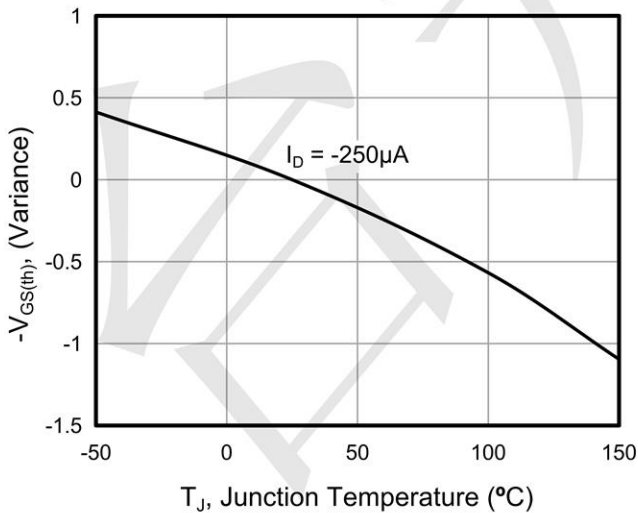


Figure 6. Body Diode Forward Voltage

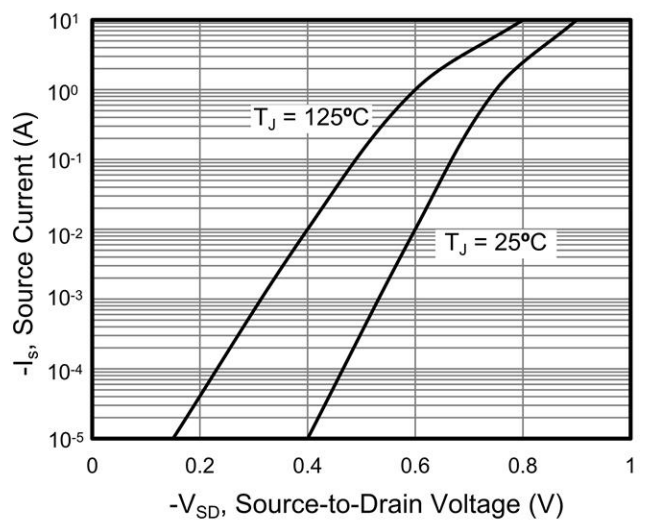


Figure 7. Capacitance

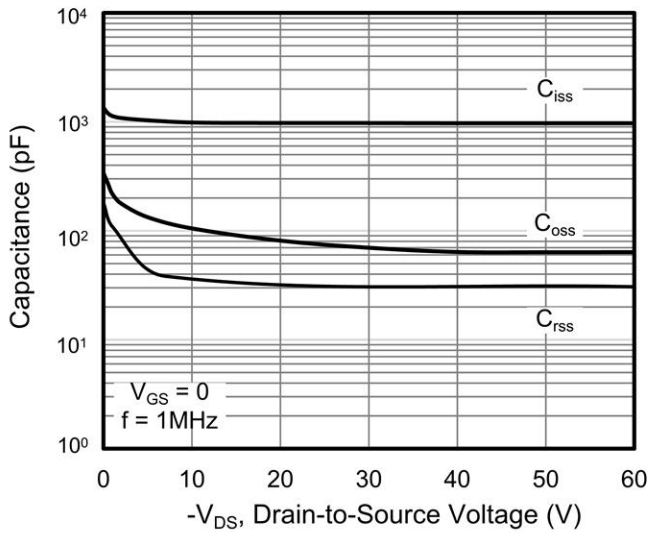


Figure 8. Gate Charge

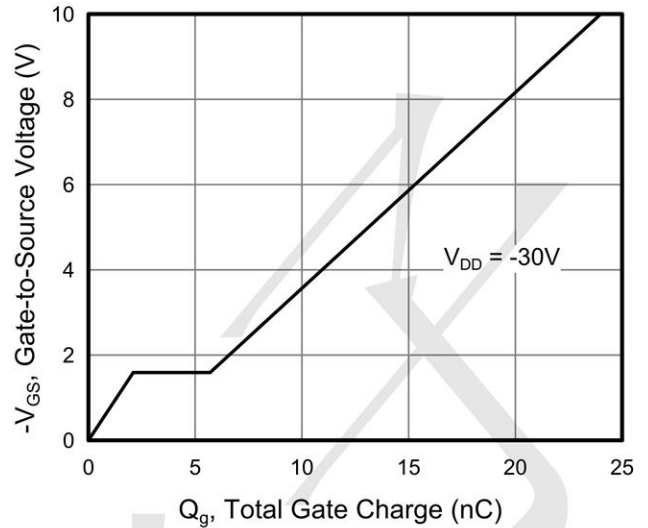


Figure 9. Transient Thermal Impedance

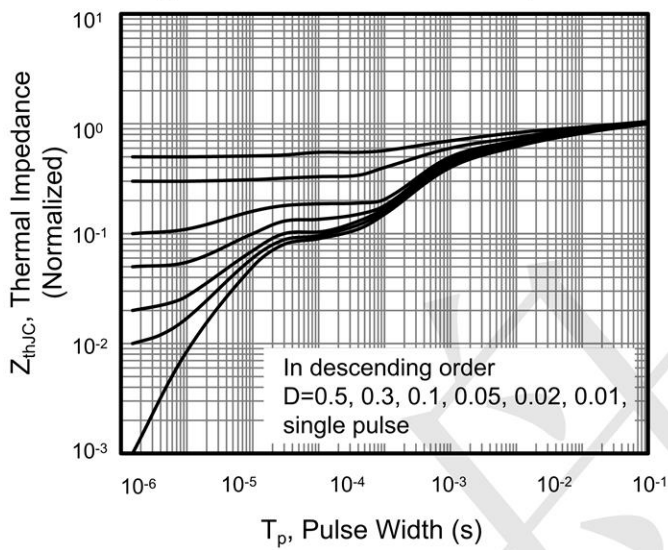
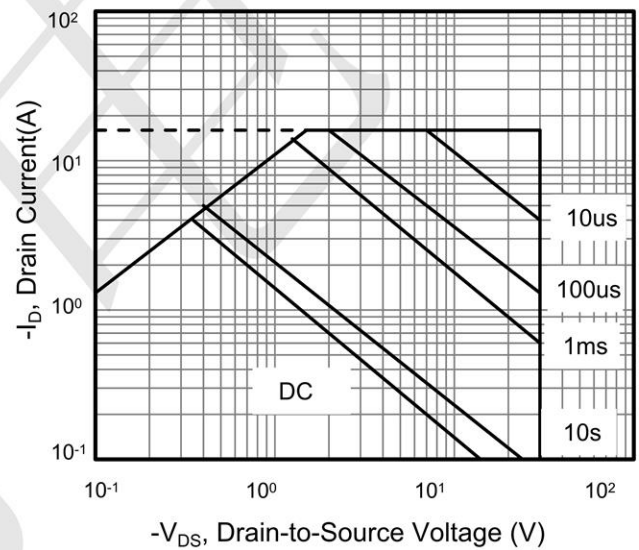
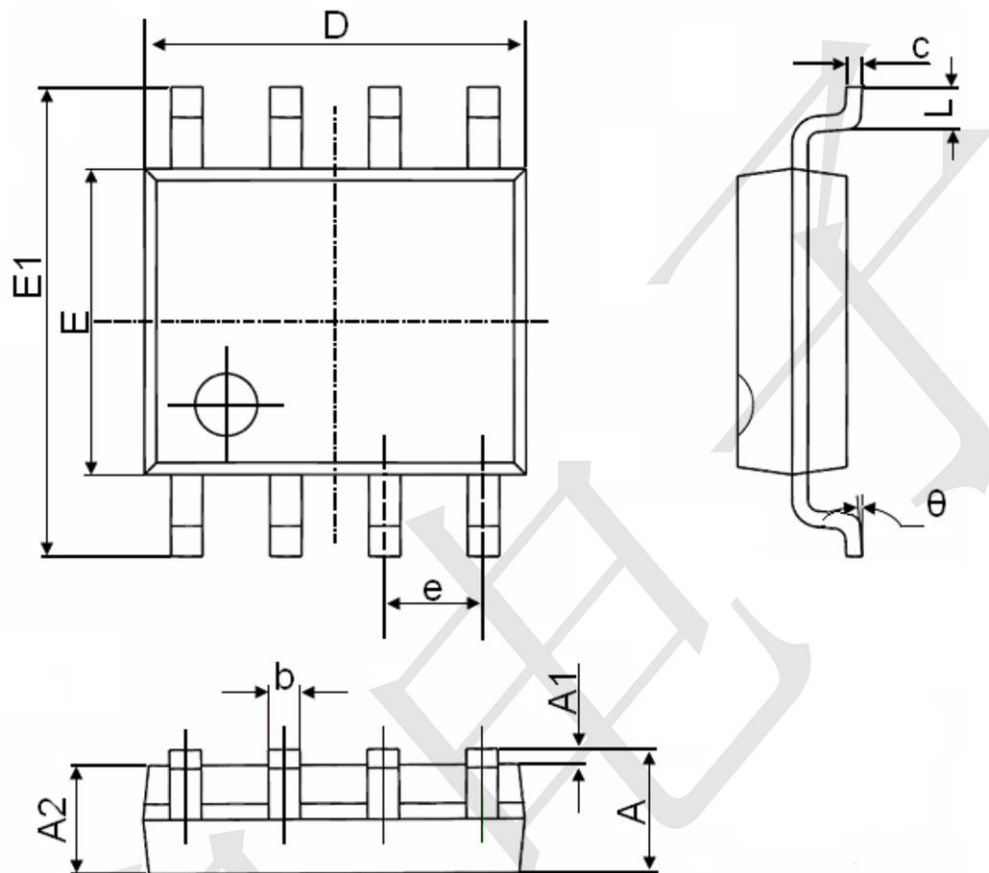


Figure 10. Safe Operating Area



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [TECH PUBLIC](#) manufacturer:*

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [2SK2267\(Q\)](#) [BUK455-60A/B](#) [TK100A10N1,S4X\(S](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#)  
[IRS2092STRPBF-EL](#) [IPS70R2K0CEAKMA1](#) [SQM120N06-3M5L-GE3](#) [TK31J60W5,S1VQ\(O](#) [TK31J60W,S1VQ\(O](#) [TK16J60W,S1VQ\(O](#)  
[2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [P85W28HP2F-7071](#) [NTE2384](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#)  
[DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)  
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [IPS60R360PFD7SAKMA1](#)  
[DMN2990UFB-7B](#) [SSM3K35CT,L3F](#) [IPLK60R1K0PFD7ATMA1](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [IPWS65R035CFD7AXKSA1](#)  
[MCQ7328-TP](#) [SSM3J143TU,LXHF](#) [PJMF280N65E1\\_T0\\_00201](#) [PJMF380N65E1\\_T0\\_00201](#) [PJMF280N60E1\\_T0\\_00201](#)  
[PJMF600N65E1\\_T0\\_00201](#) [PJMF900N65E1\\_T0\\_00201](#) [PJMF900N60E1\\_T0\\_00201](#)